



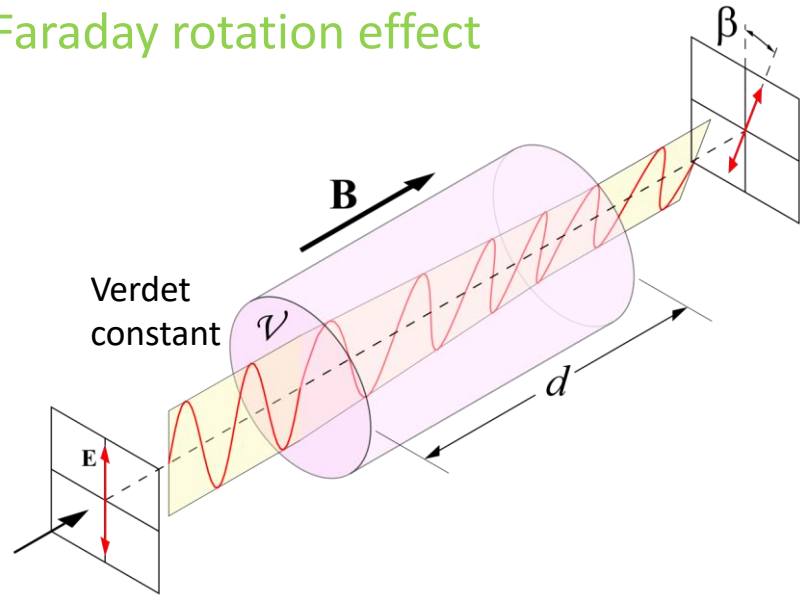
Enabling research: Silicon optics steady state magnetic field sensor

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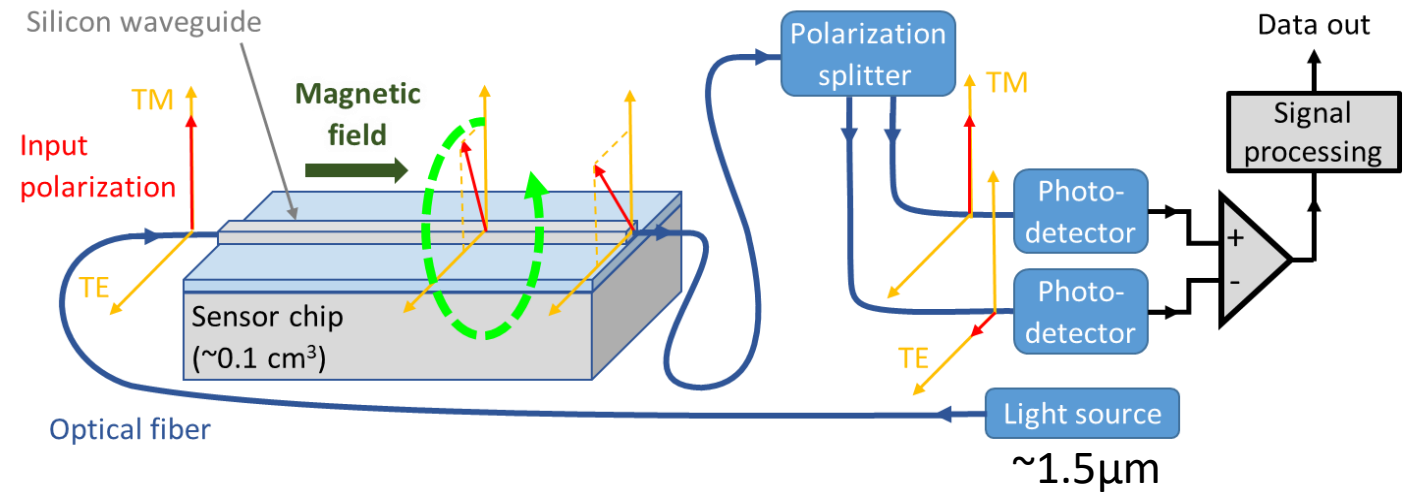


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Faraday rotation effect



Sensor on silicon (simplified schematic)



- **Aim:** develop a prototype **steady state** magnetic field sensor
- **Physics principle:** Faraday rotation of light under magnetic field influencing the output of an integrated polarization splitter
- **Technology:** Photonic integrated circuit (PIC) based on 3 μm thick silicon-on-insulator (SOI) waveguides
- **Speciality:** Folded waveguides and mirror-based U-bends to accumulate Faraday rotation, novel mirror-based polarization splitters, and a method to avoid the impact of unwanted Faraday rotation in input/output fibers

Big picture

3 μm SOI PIC platform
with passive and active
functions (schematic)

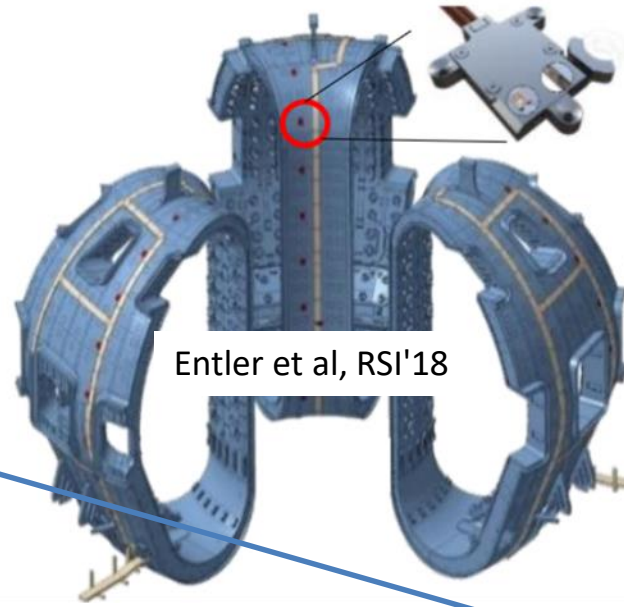
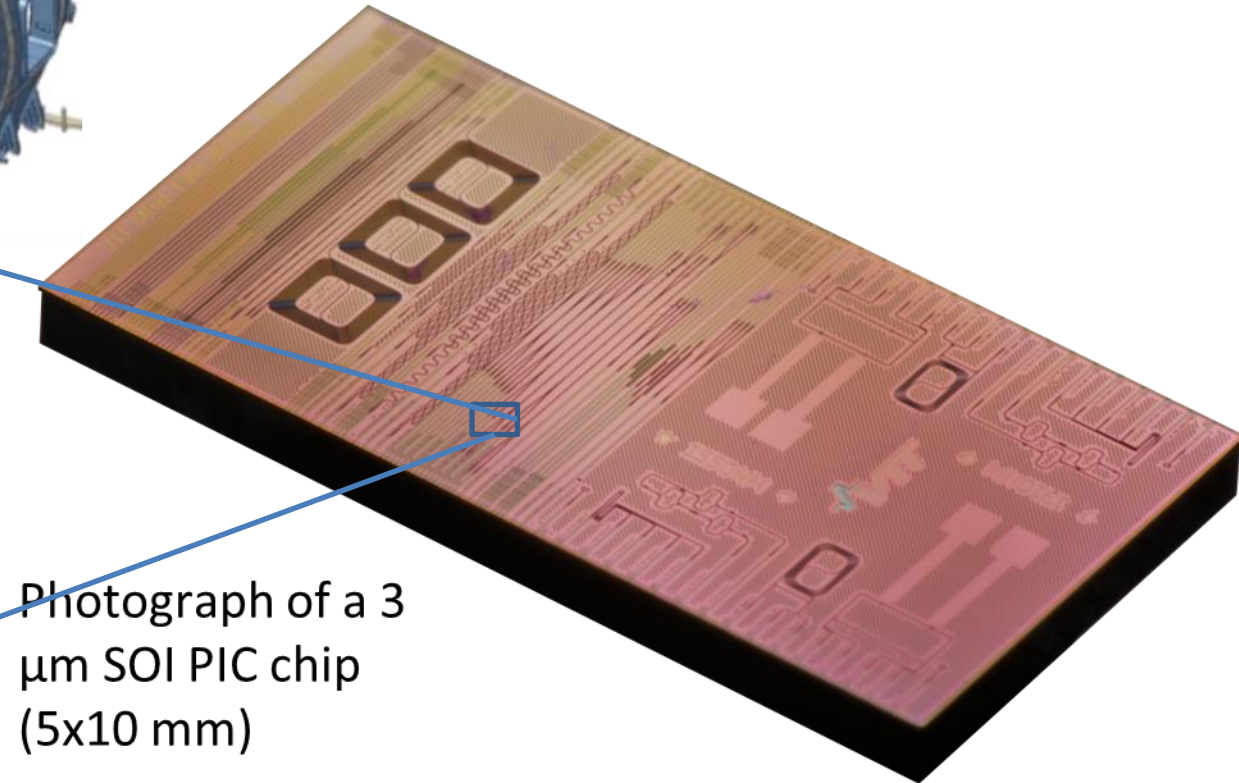
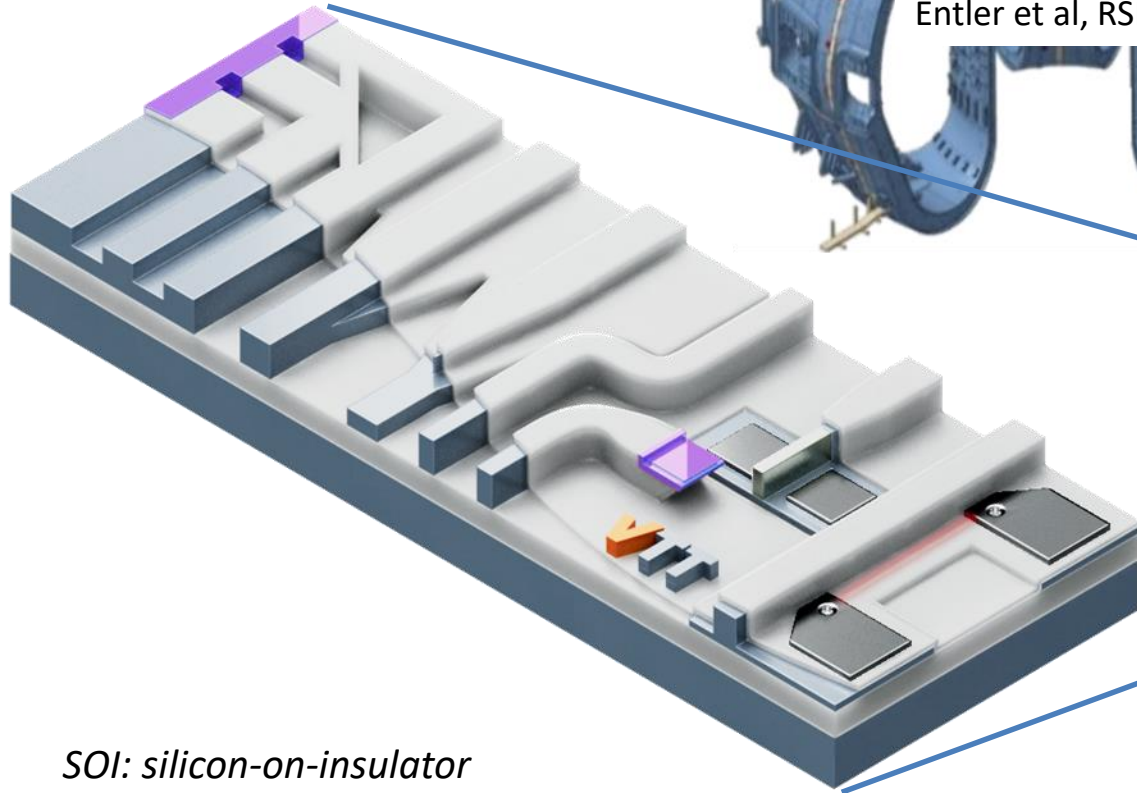


Illustration of a tokamak reactor with a
(conventional) magnetic field sensor in one
potential place for magnetic field measurement

Entler et al, RSI'18

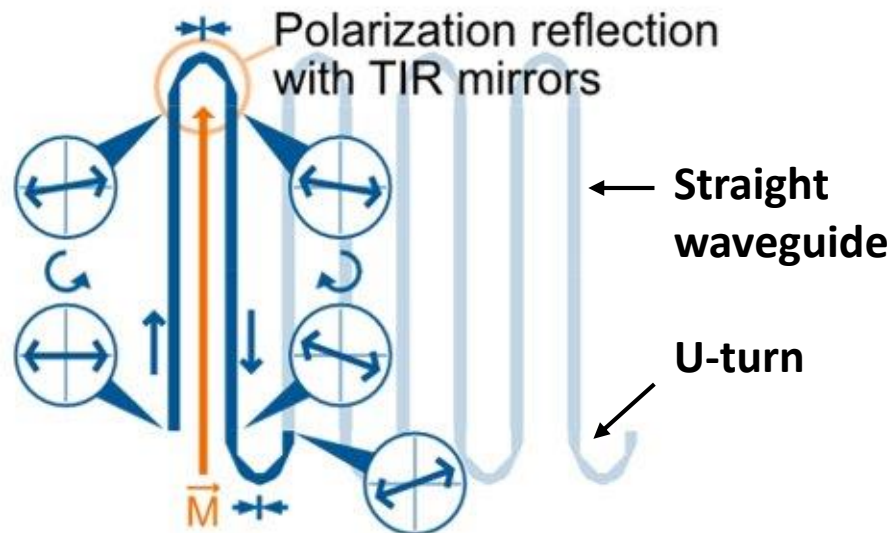


Photograph of a 3
 μm SOI PIC chip
(5x10 mm)

SOI: silicon-on-insulator
PIC: photonic integrated circuit

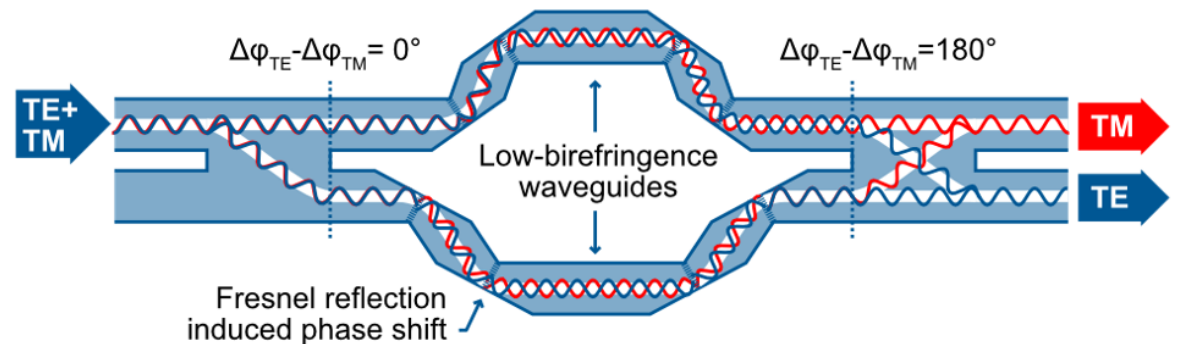
Faraday rotator based on

- **Straight waveguides** with dimensions and coating optimized for **zero birefringence**
- **Folded waveguides with U-turns** based on total internal reflection (TIR) mirrors



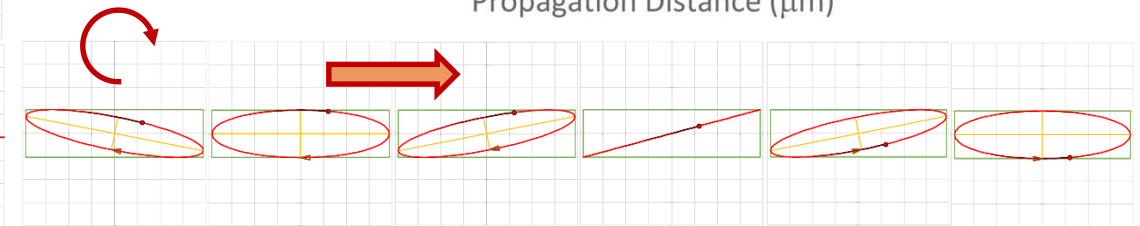
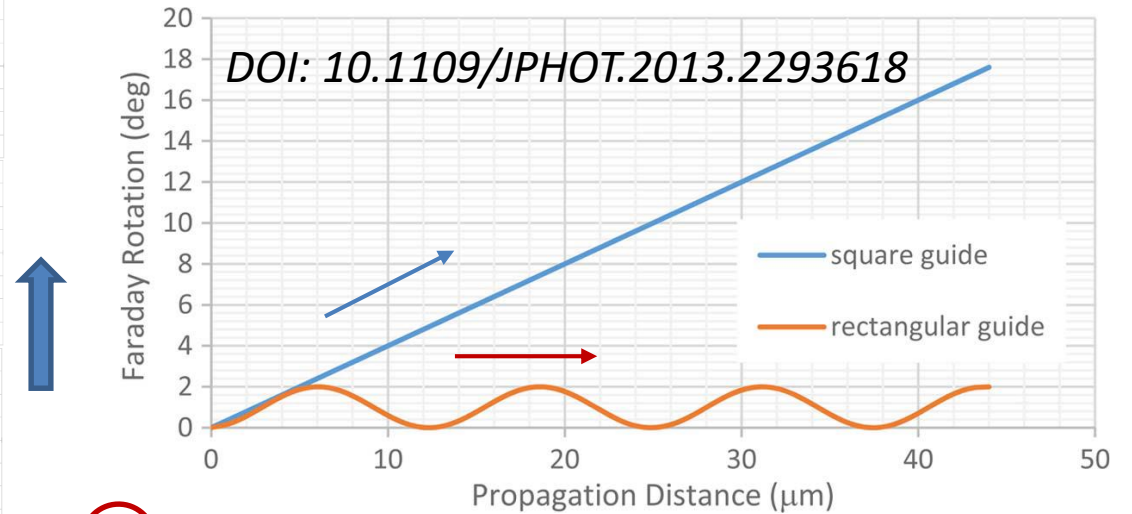
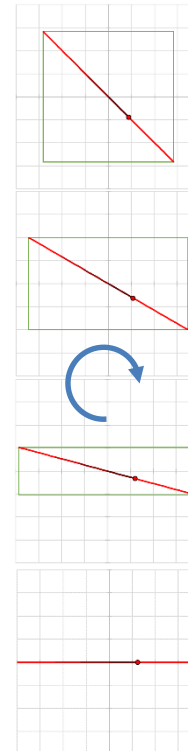
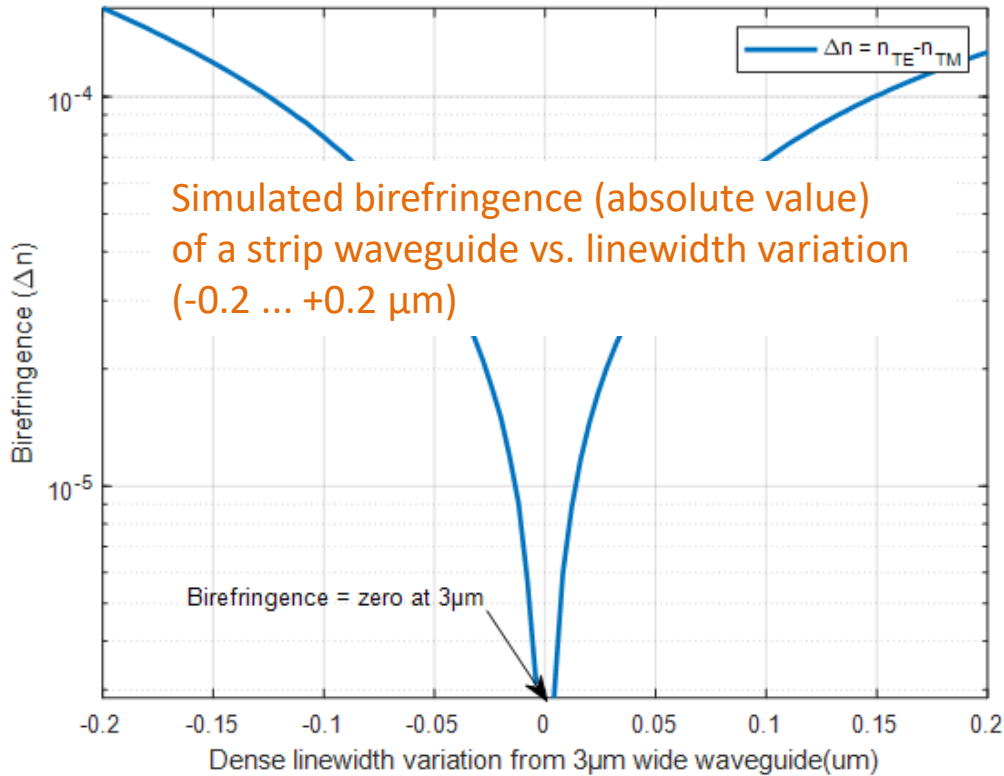
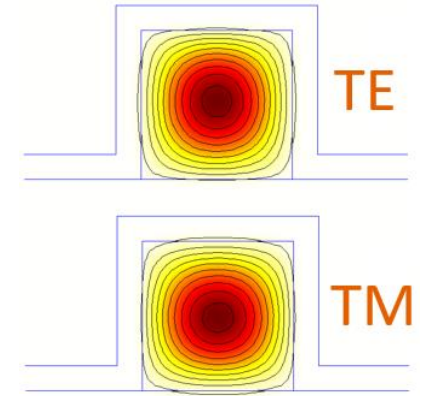
Polarisation splitter at the input and output of the Faraday rotator

- To create linear input polarization
- To measure the amount of Faraday rotation



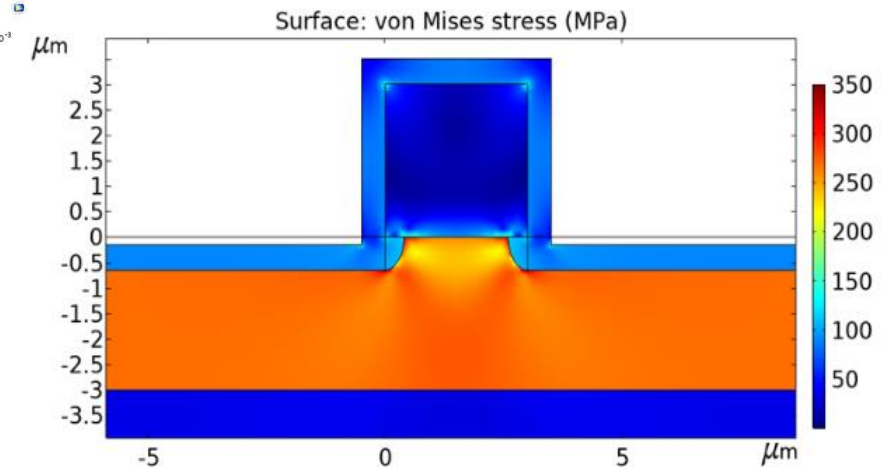
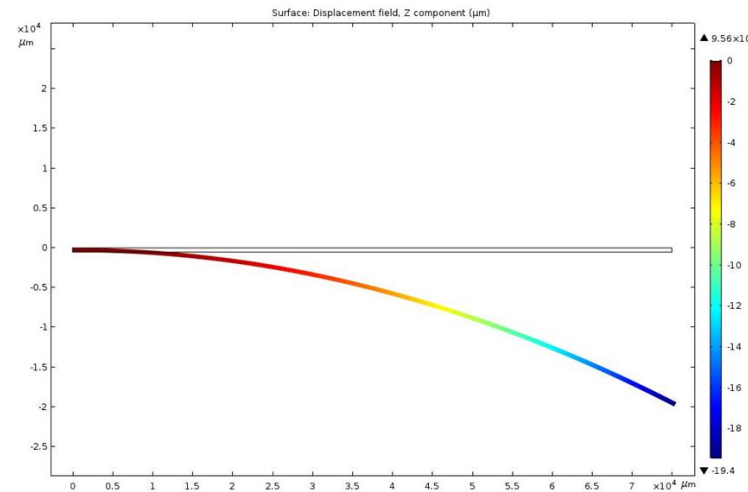
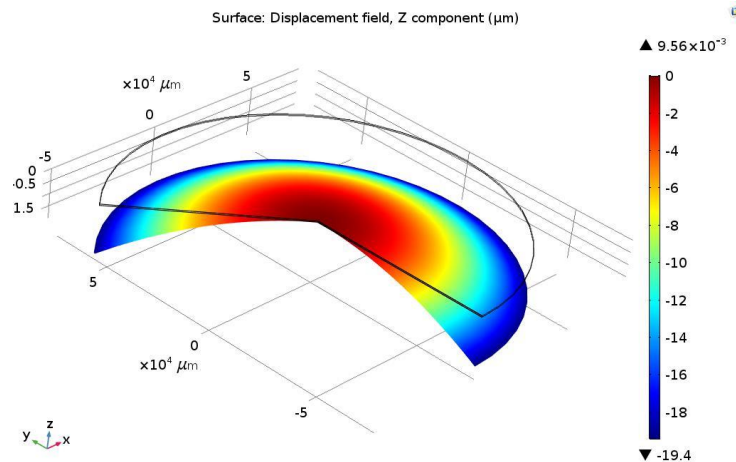
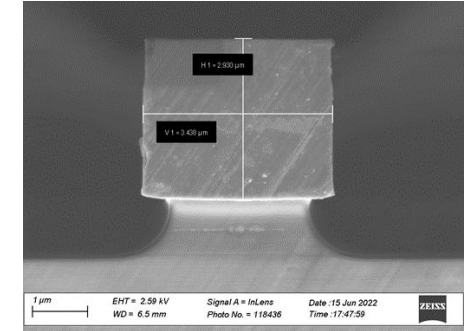
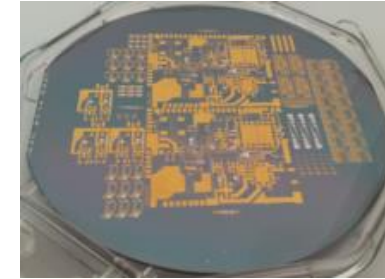
~Zero birefringence waveguides

- Zero birefringence of waveguides is needed for efficient Faraday rotation (as in the blue line)
- Stress free 3 μm wide strip waveguide can produce zero birefringence, but needs good linewidth control



Experimentally inferred oxide stress values

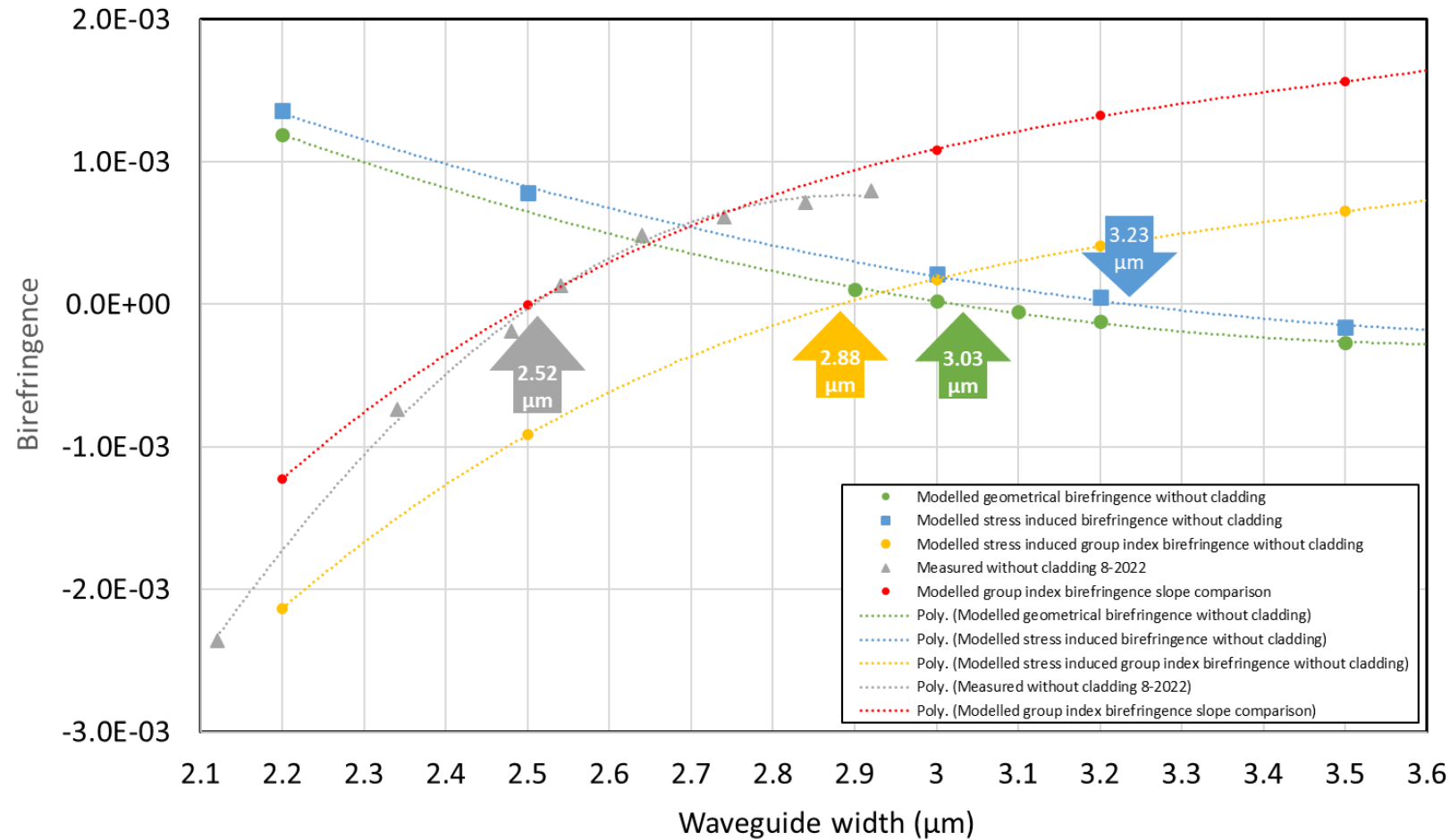
- Oxides on silicon monitor wafers
 - Bow measurements before and after oxide deposition
 - COMSOL modelling to define corresponding wafer bending value
- ⇒ Experimentally defined stress value



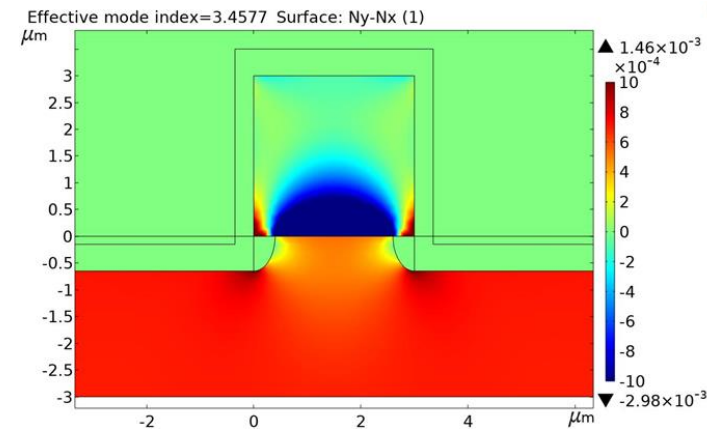
3D axisymmetric model

- Experimentally defined SOI-SiO2 BOX oxide stress -350 MPa

Birefringence for 3µm thick strip waveguide without cladding
Experimentally defined SOI-SiO2 oxide stress -350/0 MPa

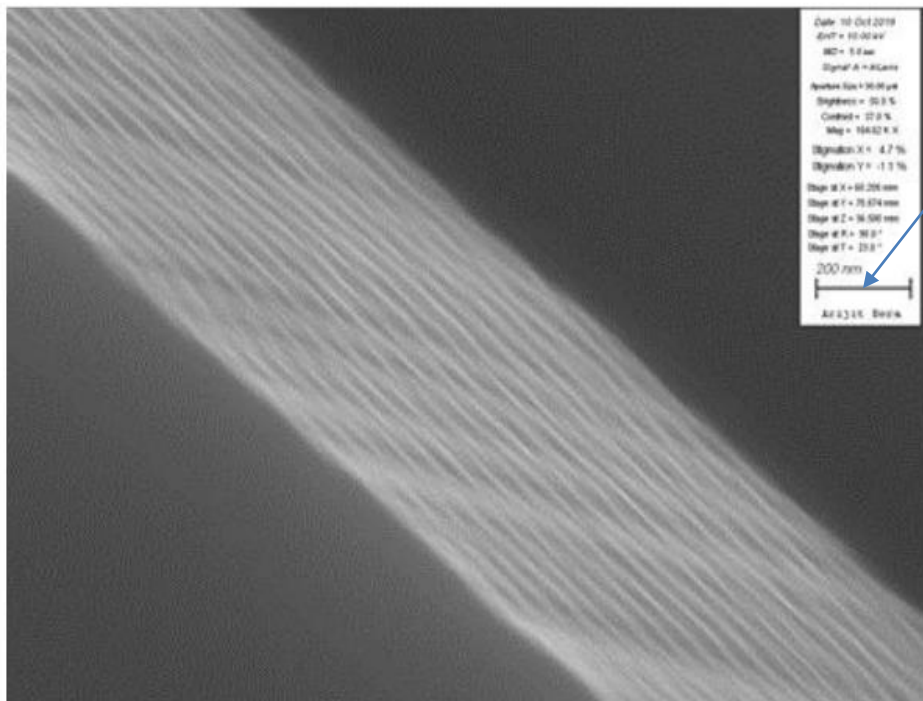


$$n_g = n_{\text{eff}} - \frac{\lambda dn_{\text{eff}}}{d\lambda}$$



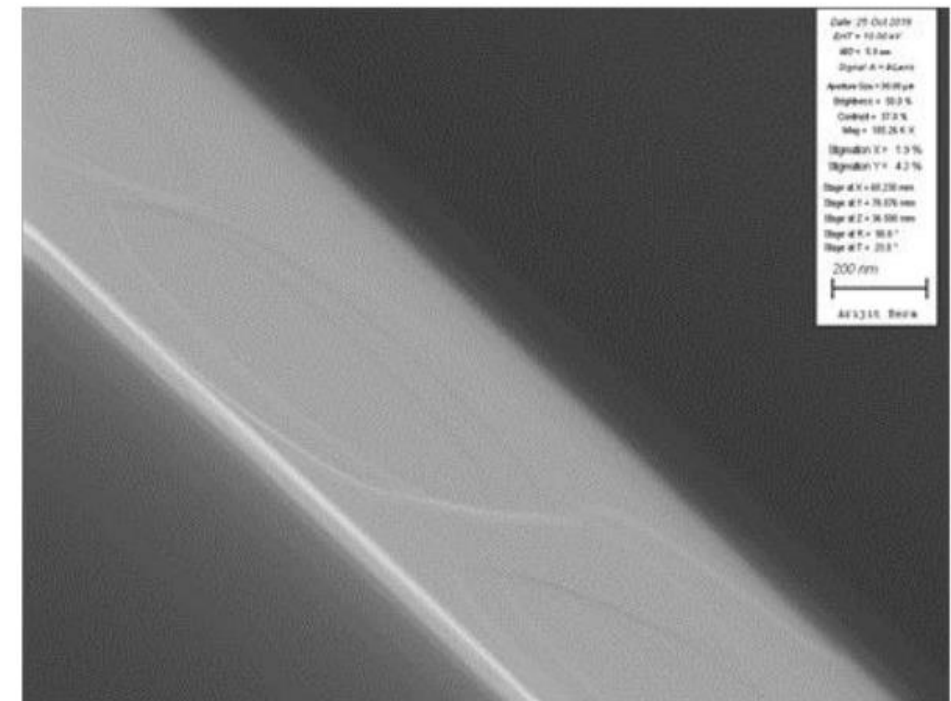
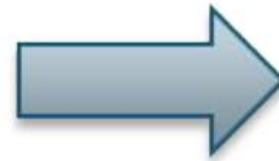
Hydrogen annealing for smoother waveguides

- SEM images of Hydrogen annealed waveguide surface after 15 min treatment
- Measurements show 75% improvement in polarisation extinction ratio and attenuation down to 4 dB/m

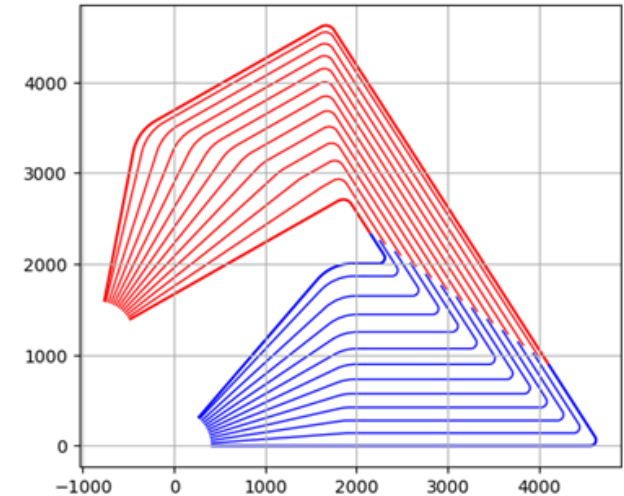


200 nm

Annealed
for 15 min

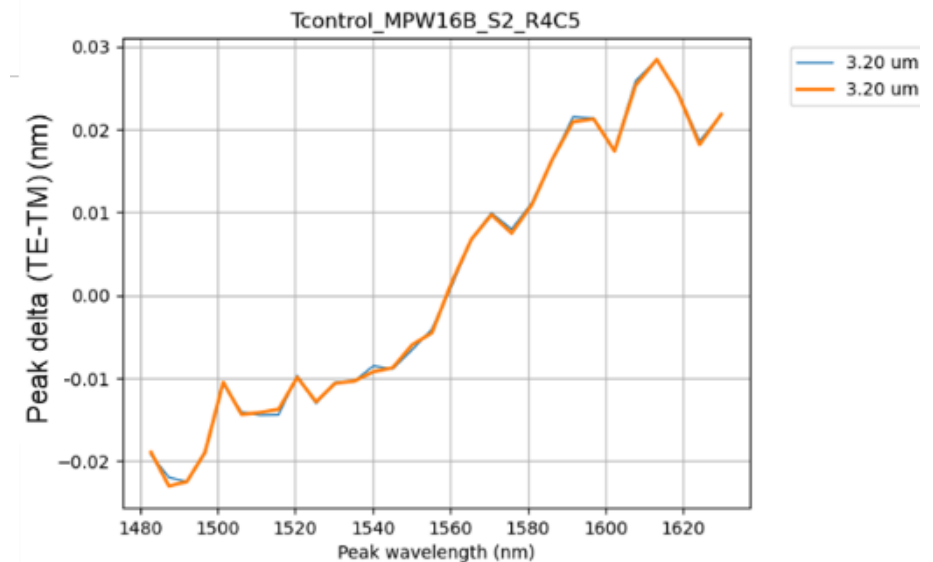
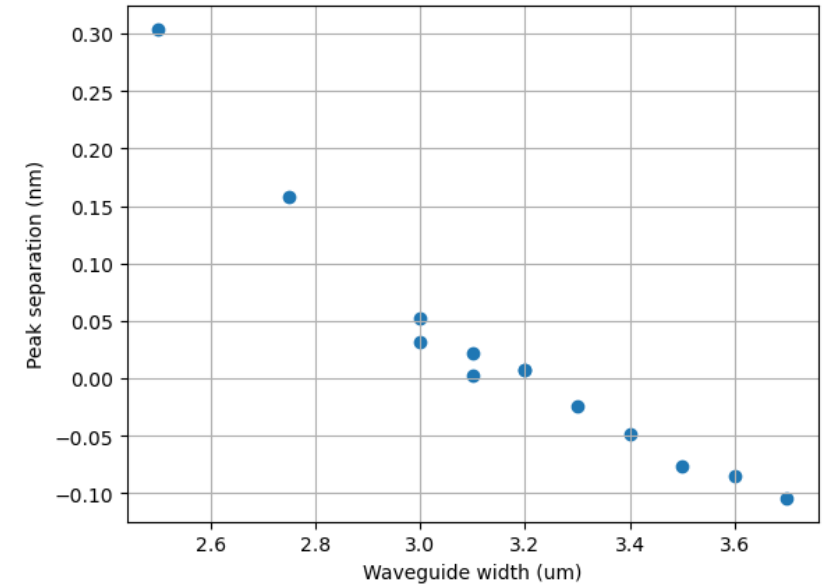
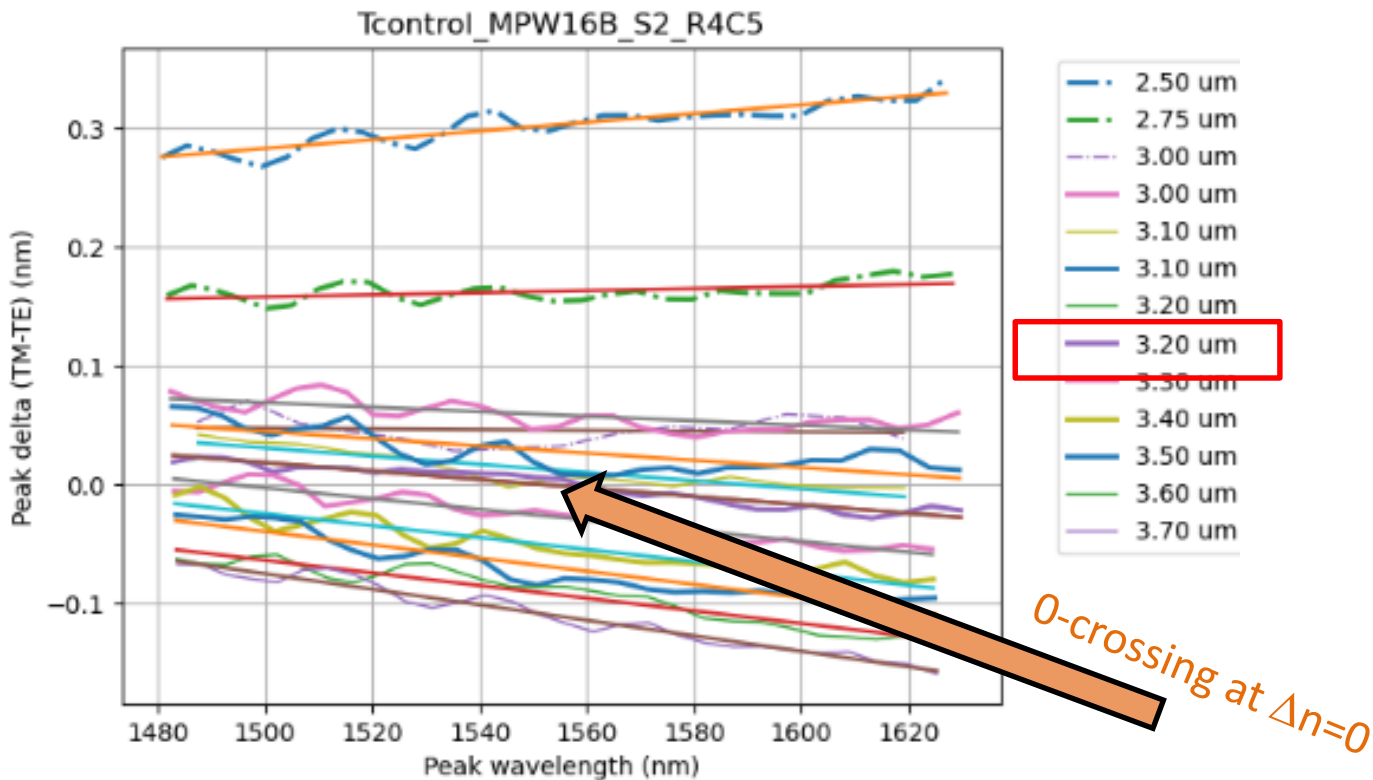


- Effective index birefringence cannot be measured from a single waveguide
 - Specific test structures are needed for each waveguide dimension of interest
- Two approaches utilised
 - Arrayed waveguide gratings (AWG)
 - Folded waveguides with a 3-point scan in straight section lengths

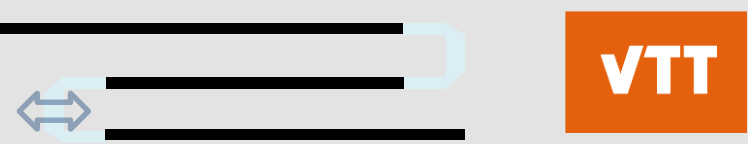


AWG measurements

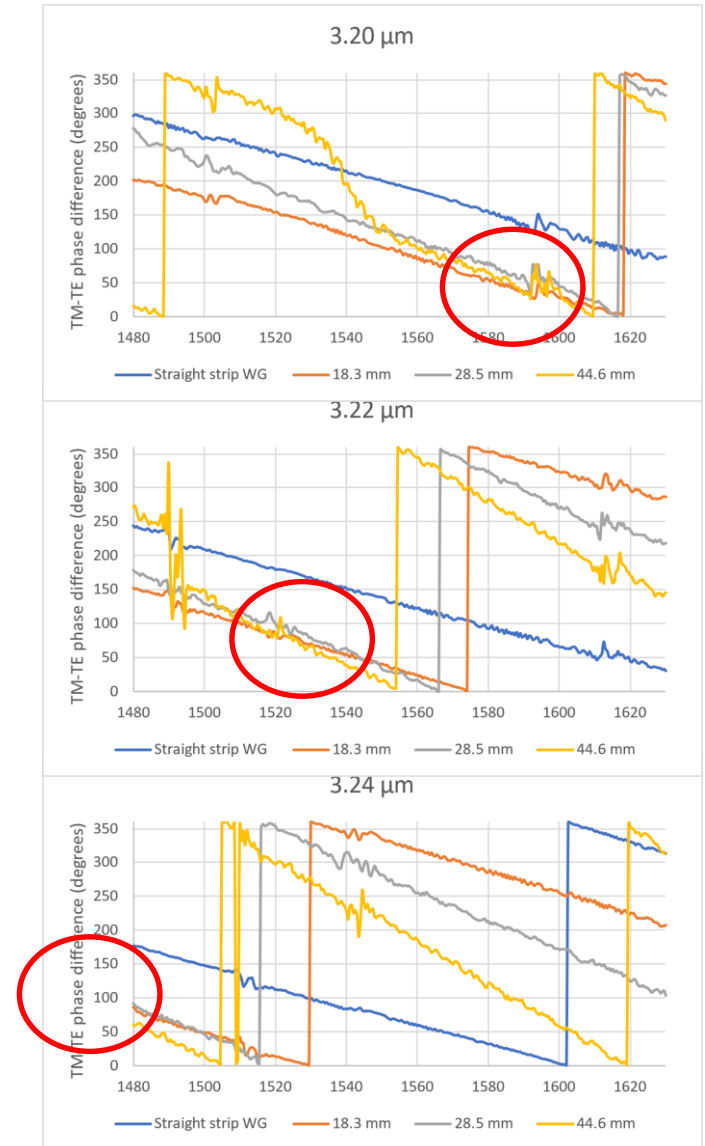
- Rough scan of waveguide widths point to 3.2 μm
- Measurement noise is small as seen from repeat measurement
 - Small scale variation likely due to 3D roughness of the waveguide surfaces



Folded waveguide

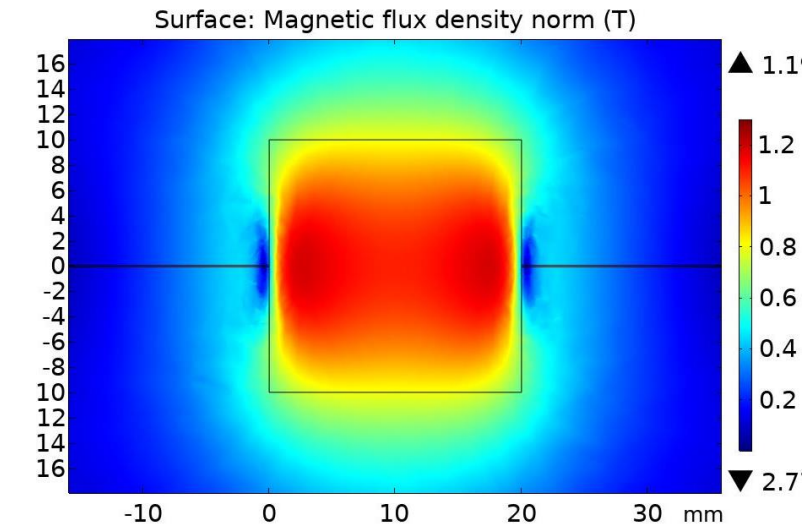
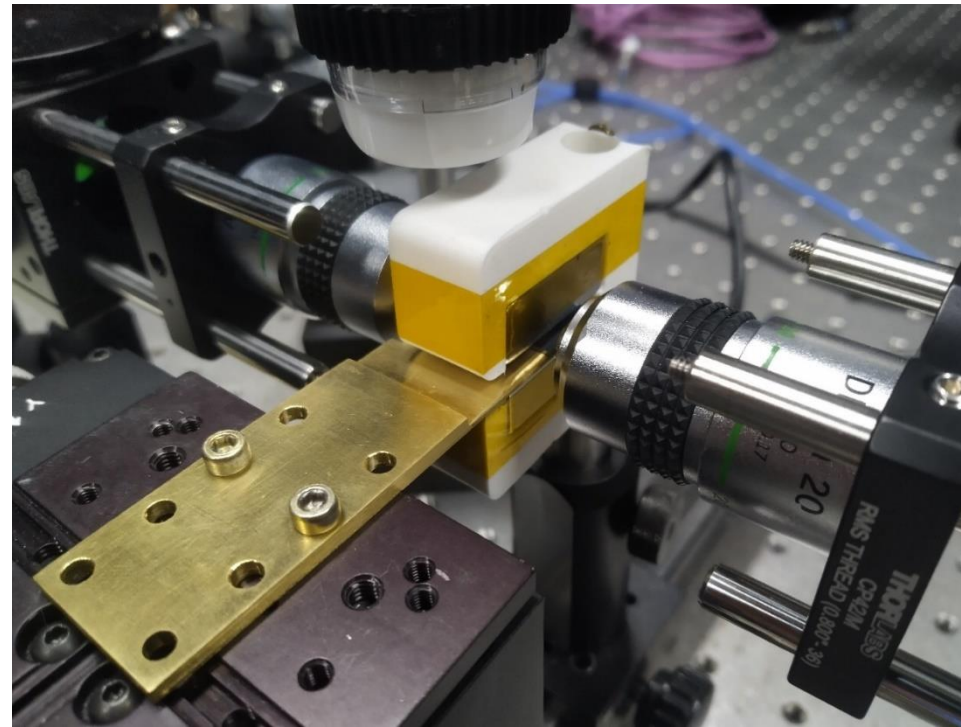


- Test structures from the same wafer show the same width for the minimum birefringence $\sim 3.2\mu\text{m}$
- The location of the 3-way crossing point moves to smaller wavelength with increasing width similar to AWG measurements
- NB: waveguides from another processing run have the crossing near $\sim 3.1\mu\text{m}$ indicating sensitivity to the exact manufacturing 'recipe'



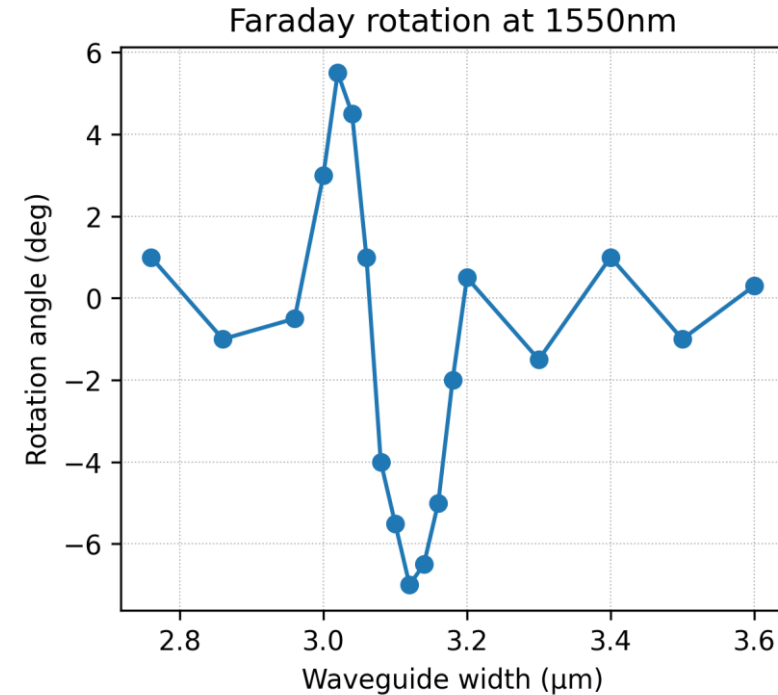
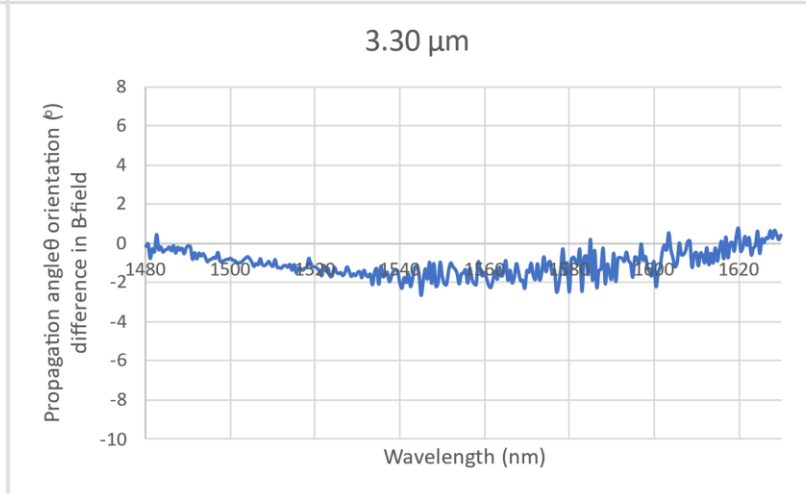
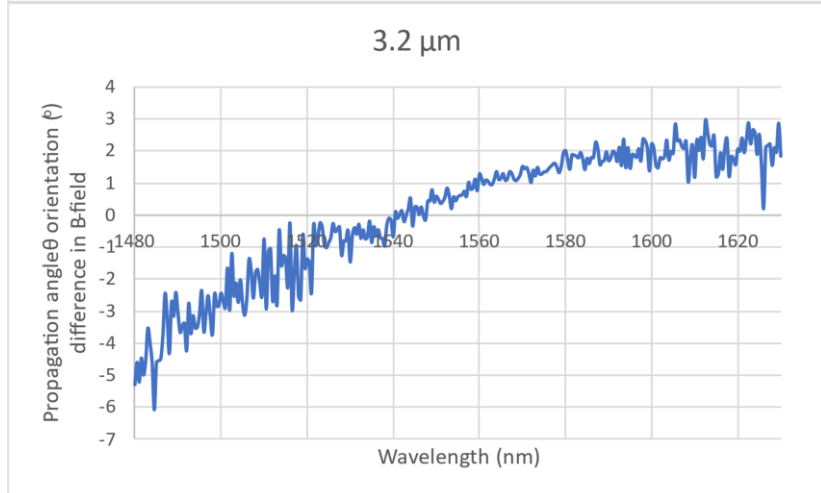
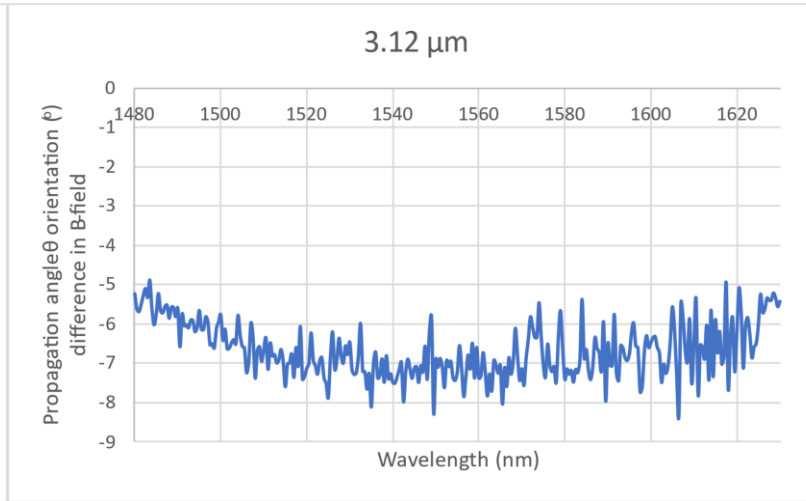
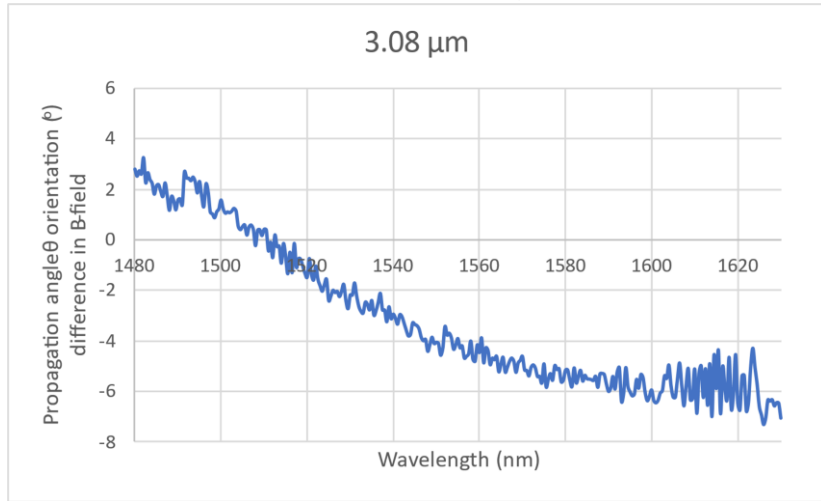
Faraday rotation measurement setup

- Movable permanent magnet with 1 T allows clean measurement of with and without magnetic field
 - COMSOL calculations confirm magnetic field uniformity



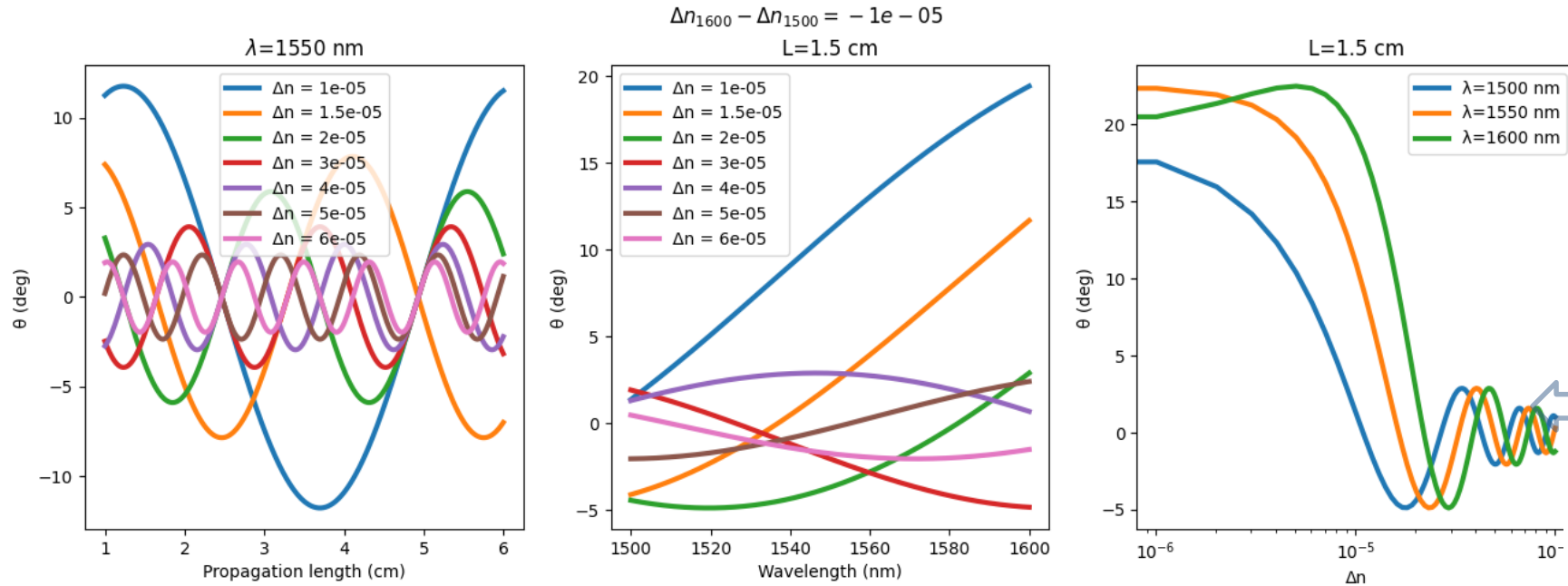
Rotation angle difference measurement @1T

- Rotation angle should be $\sim 22.5\text{deg}$ for *Verdet constant* 15 [deg/T/cm] at zero birefringence
- Is this Faraday rotation?

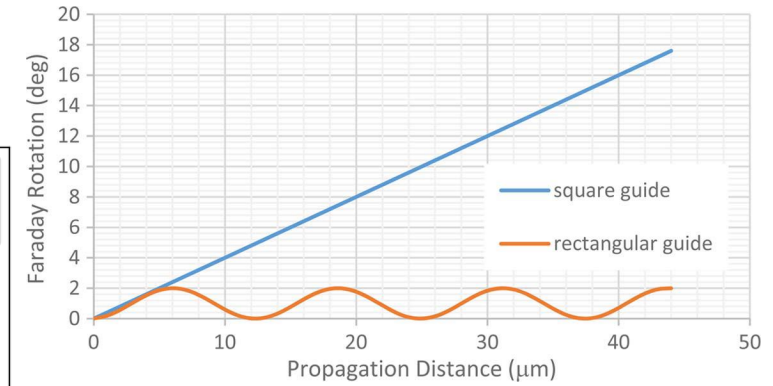


Faraday rotation

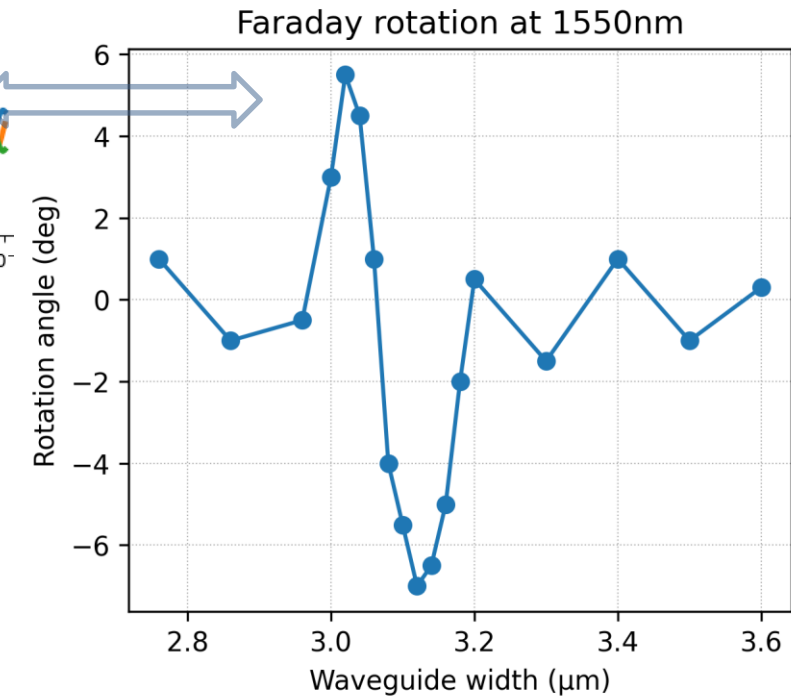
- $\theta = B_{field} \cdot Length \cdot V_{erdet} \cdot \text{sinc } f(\Delta n, \lambda, Length)$



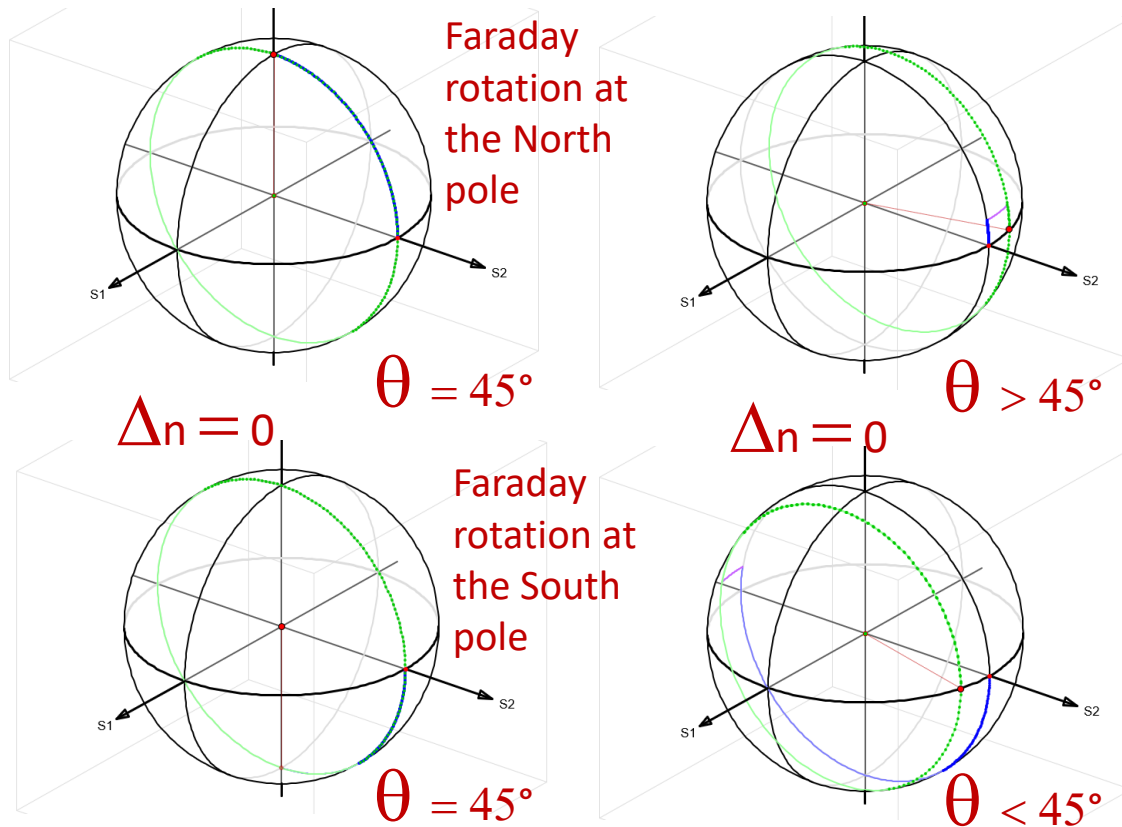
2014: Review in Photonics Journal, IEEE



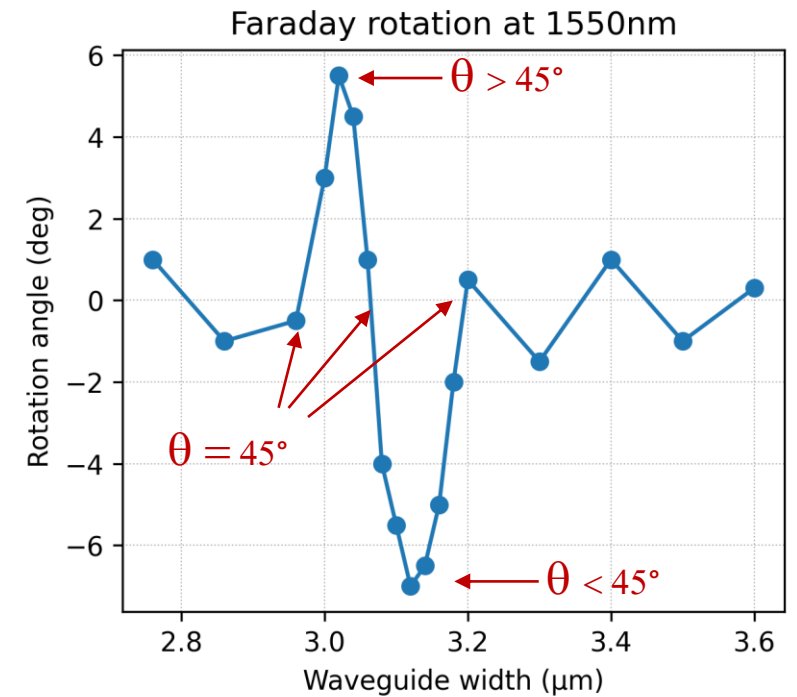
- Clear Faraday rotation measured but due to too high birefringence variation, rotation does not accumulate but oscillates
- High sensitivity not feasible by increasing waveguide length



- Approximately the same Faraday rotation around zero birefringence, but different TE-TM phase differences for different widths
- No Faraday rotation in the North or South pole



Faraday rotation near the equator, but with opposite TE-TM phase differences, leading to opposite changes in θ



- COMSOL modelling using the inferred stress values are in fair agreement with measurements
- Faraday effect was demonstrated successfully but found to be in the non-ideal regime owing to the sensitivity of Faraday rotation to birefringence.
- The inherently high birefringence variation of the 3 μm silicon waveguide makes it difficult to obtain highly sensitive magnetic field sensor as targeted
- TIR mirror based $n \cdot \pi$ phase difference U-bends manufactured exhibited larger loss of light than expected (compared to test structures) for yet unknown reasons